

Automotive MOSFET

OptiMOS™ 5 Power-Transistor



Features

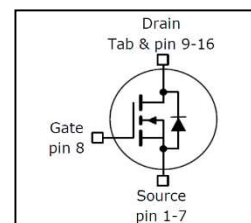
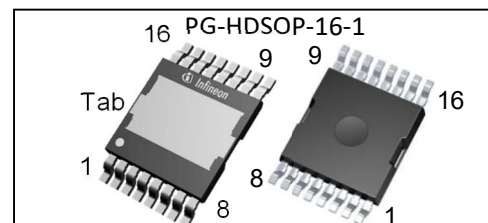
- OptiMOS™ power MOSFET for automotive applications
- N-channel – enhancement mode – normal level
- Extended qualification beyond AEC-Q101
- Enhanced electrical testing
- Robust design
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- RoHS compliant
- 100% avalanche tested

Potential applications

General automotive applications.

Product validation

Qualified for automotive applications. Product validation according to AEC-Q101.



Product Summary

V_{DS}	60	V
$R_{DS(on)}$	0.79	mΩ
I_D (chip limited)	503	A

Type	Package	Marking
IAUTN06S5N008T	PG-HDSOP-16-1	5N06N008

Table of Contents

Description	1
Maximum ratings	3
Thermal characteristics	4
Electrical characteristics	4
Electrical characteristics diagrams	6
Package outline & footprint	10
Revision history	11
Disclaimer	12

Maximum ratings

at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$V_{GS}=10\text{ V}$, Chip limitation ^{1,2)}	503	A
		$V_{GS}=10\text{ V}$, DC current ³⁾	350	
		$T_a=100\text{ °C}$, $V_{GS}=10\text{ V}$, R_{thJA} on top ^{2,4)}	136	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$, $t_p=100\text{ }\mu\text{s}$	1940	
Avalanche energy, single pulse ²⁾	E_{AS}	$I_D=175\text{ A}$	940	mJ
Avalanche current, single pulse	I_{AS}	–	350	A
Gate source voltage	V_{GS}	–	± 20	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	358	W
Operating and storage temperature	T_j, T_{stg}	–	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	–	–	55/175/56	

Thermal characteristics²⁾

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	Top	-	-	0.42	K/W
		Bottom (Pin 1-7)	-	9	-	
		Bottom (Pin 9-16)	-	3	-	
Thermal resistance, junction - ambient ⁴⁾	R_{thJA}	Top	-	2.8	-	
		Bottom (through PCB)	-	40	-	

Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Static characteristics

Drain-source breakdown voltage	$V_{(Br)DSS}$	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$	60	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=275\text{ }\mu\text{A}$	2.2	2.6	3.0	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$	-	0.1	1	μA
		$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=100\text{ °C}^{2)}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=7\text{ V}$, $I_D=50\text{ A}$	-	0.72	0.90	m Ω
		$V_{GS}=10\text{ V}$, $I_D=100\text{ A}$	-	0.63	0.79	
Gate resistance ²⁾	R_G	-	-	1.8	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics²⁾

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=30\text{ V}, f=1\text{ MHz}$	–	15600	20280	pF
Output capacitance	C_{oss}		–	3200	4160	
Reverse transfer capacitance	C_{rss}		–	110	165	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=30\text{ V}, V_{GS}=10\text{ V},$ $I_D=100\text{ A}, R_G=3.5\ \Omega$	–	43	–	ns
Rise time	t_r		–	66	–	
Turn-off delay time	$t_{d(off)}$		–	115	–	
Fall time	t_f		–	86	–	

Gate Charge Characteristics²⁾

Gate to source charge	Q_{gs}	$V_{DD}=30\text{ V}, I_D=100\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	–	64	83	nC
Gate to drain charge	Q_{gd}		–	36	54	
Gate charge total	Q_g		–	210	273	
Gate plateau voltage	$V_{plateau}$		–	4.1	–	V

Reverse Diode

Diode continuous forward current ²⁾	I_S	$T_C=25\text{ °C}$	–	–	503	A
Diode pulse current ²⁾	$I_{S,pulse}$	$T_C=25\text{ °C}, t_p=100\ \mu\text{s}$	–	–	1940	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=100\text{ A}, T_J=25\text{ °C}$	–	0.82	0.92	V
Reverse recovery time ²⁾	t_{rr}	$V_R=30\text{ V}, I_F=50\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	–	57	86	ns
Reverse recovery charge ²⁾	Q_{rr}		–	64	128	nC

¹⁾ Practically the current is limited by the overall system design including the customer-specific PCB.

²⁾ The parameter is not subject to production testing – specified by design.

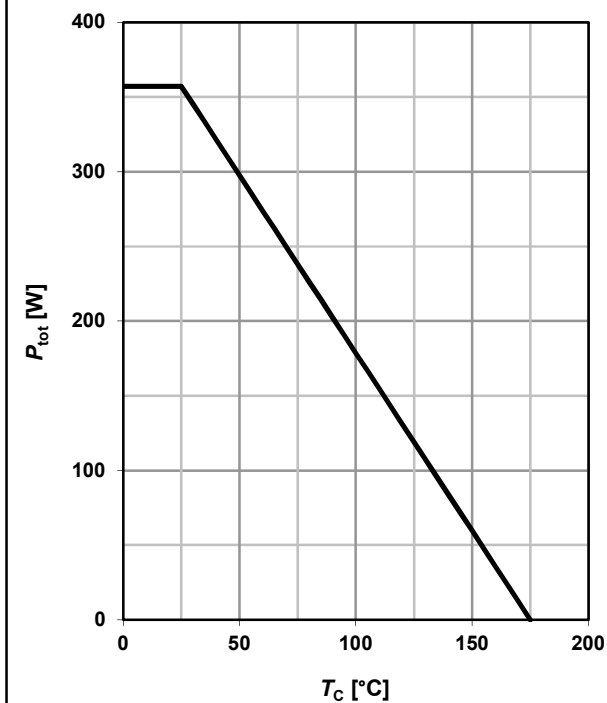
³⁾ Current is limited by package.

⁴⁾ Device on a four-layer 2s2p FR4 PCB with topside cooling. Thermal insulation material is 100 μm thick and has a conductivity of 0.7 W/m/K. Top surface of heat sink is fixed at ambient temperature. Bottom surface of PCB is left at free convection. Values may vary depending on the customer-specific design.

Electrical characteristics diagrams

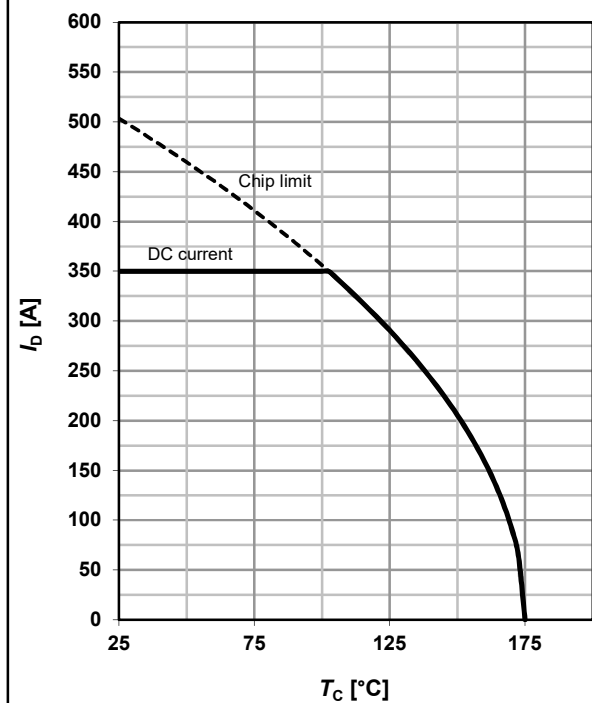
1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



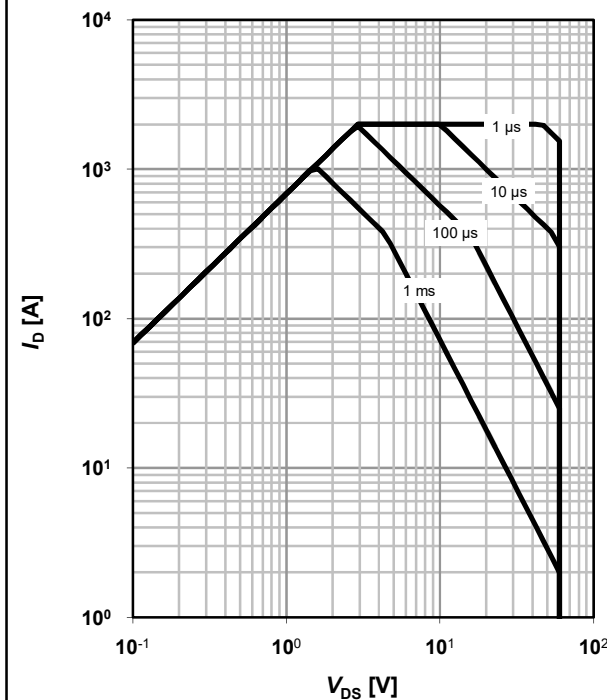
2 Drain current

$$I_D = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



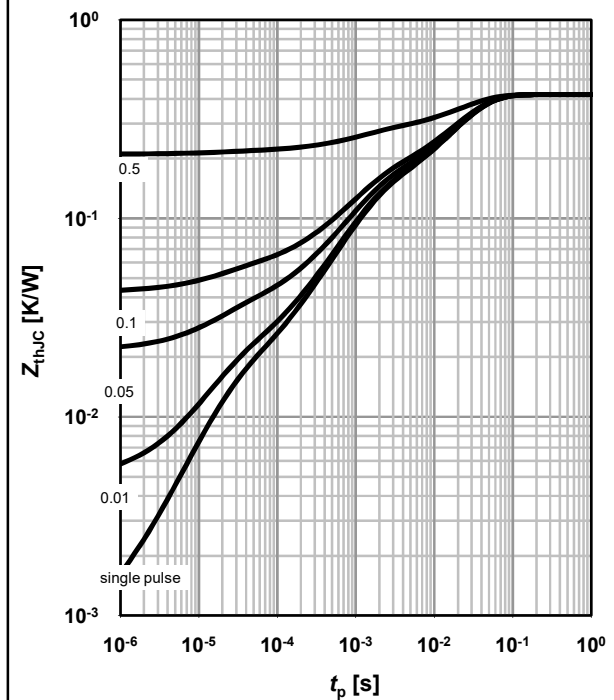
3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25 \text{ °C}; D = 0; \text{ parameter: } t_p$$



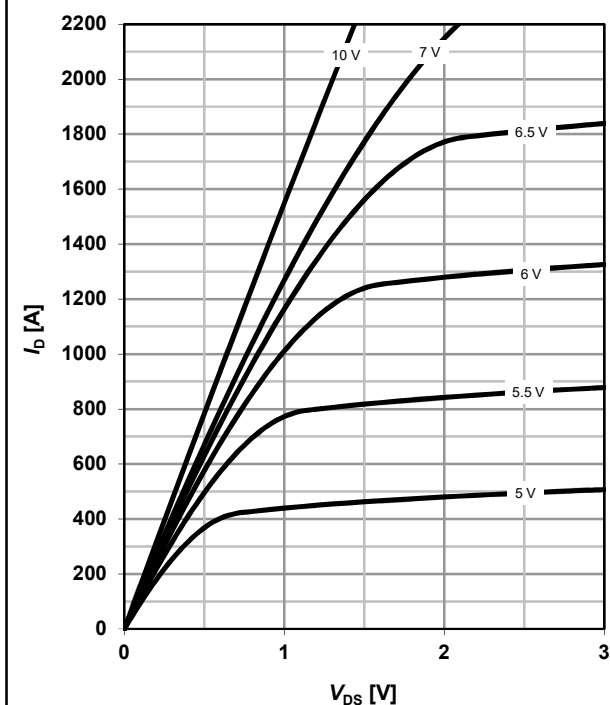
4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p); \text{ parameter: } D = t_p/T$$



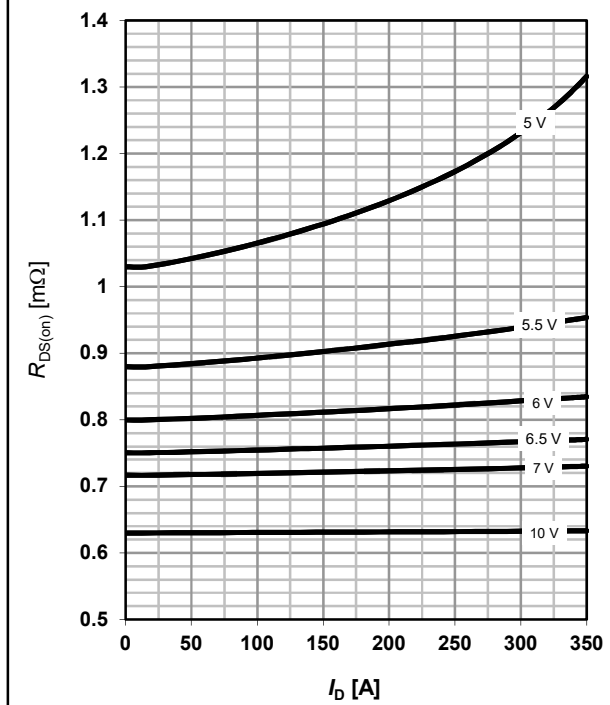
5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$



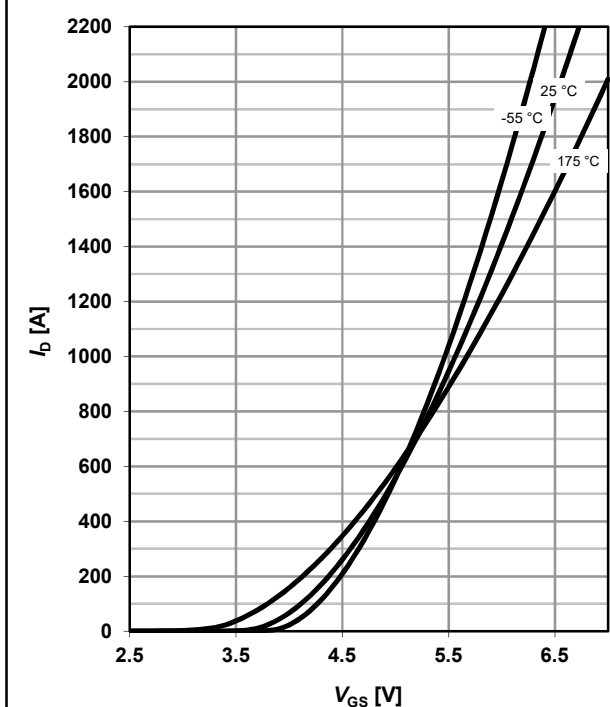
6 Typ. drain-source on-state resistance

$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$



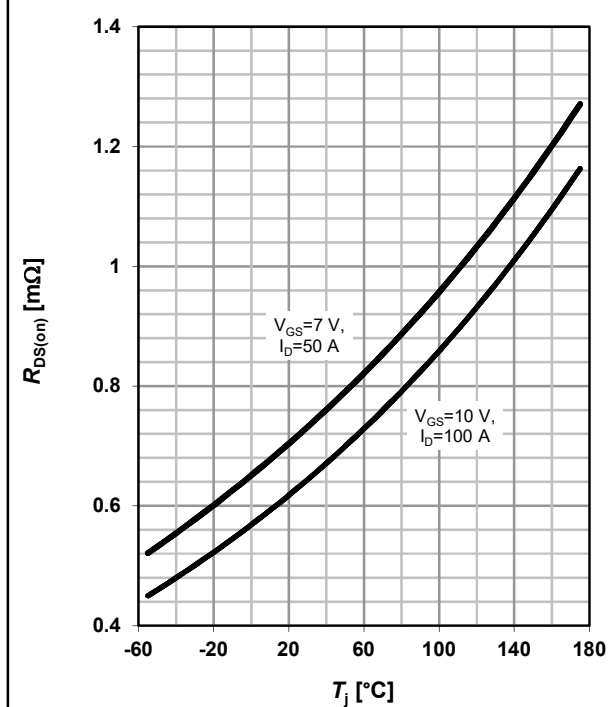
7 Typ. transfer characteristics

$I_D = f(V_{GS}); V_{DS} = 6\text{V}; \text{parameter: } T_j$



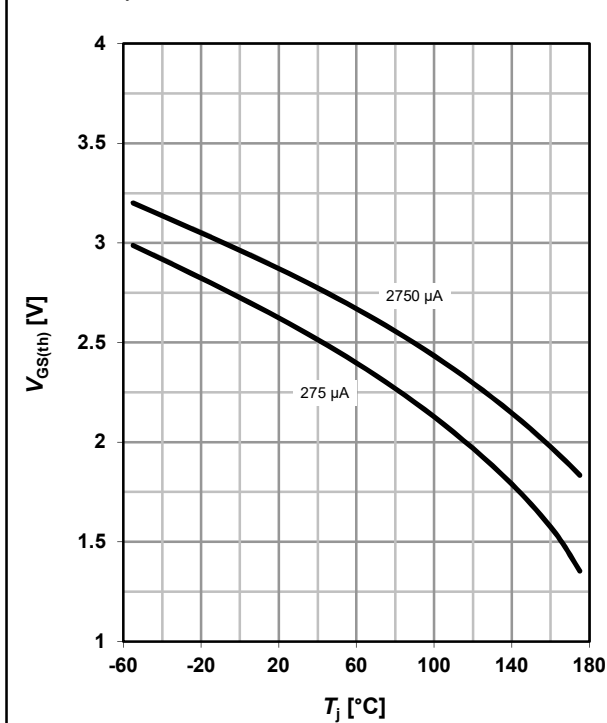
8 Typ. drain-source on-state resistance

$R_{DS(on)} = f(T_j); \text{parameter: } I_D, V_{GS}$



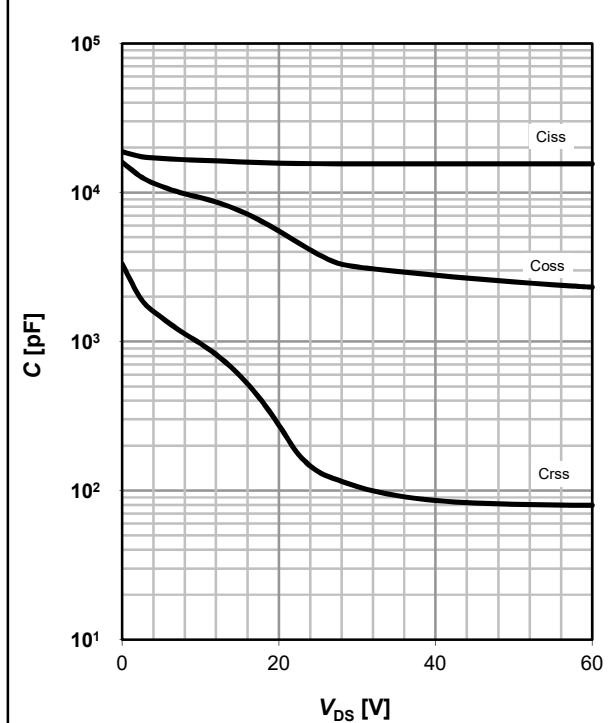
9 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$; parameter: I_D



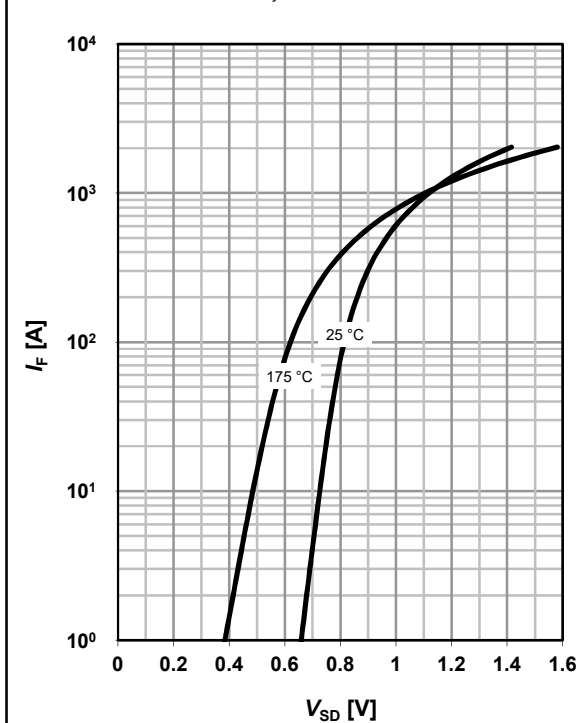
10 Typ. capacitances

$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz



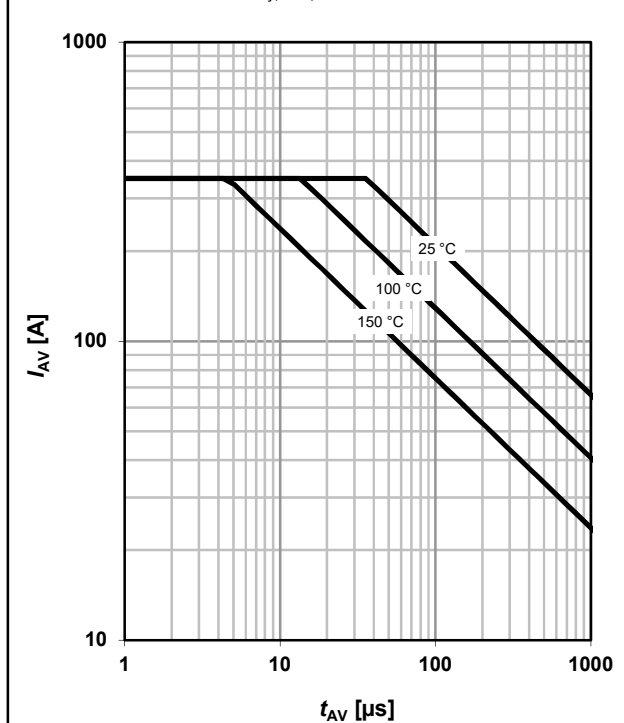
11 Typical forward diode characteristics

$I_F = f(V_{SD})$; parameter: T_j



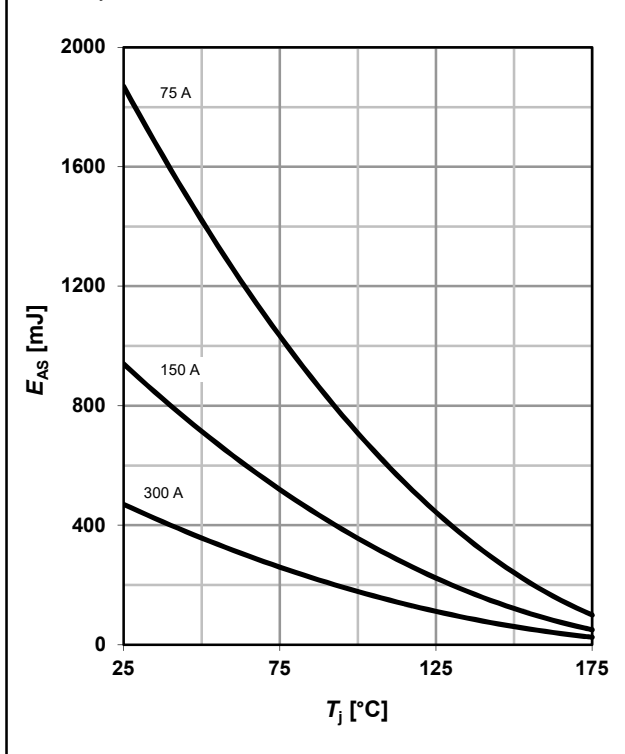
12 Typ. avalanche characteristics

$I_{AS} = f(t_{AV})$; parameter: $T_{j(start)}$



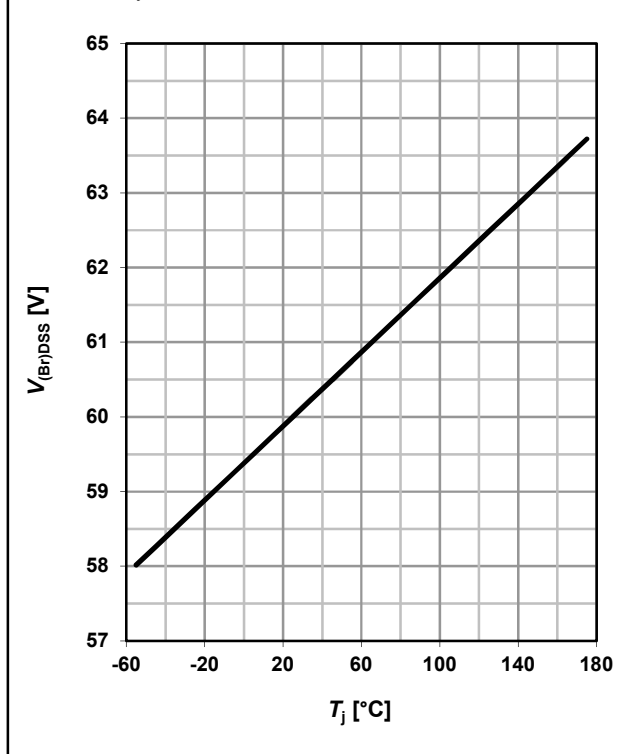
13 Typical avalanche energy

$E_{AS} = f(T_j)$; parameter: I_D



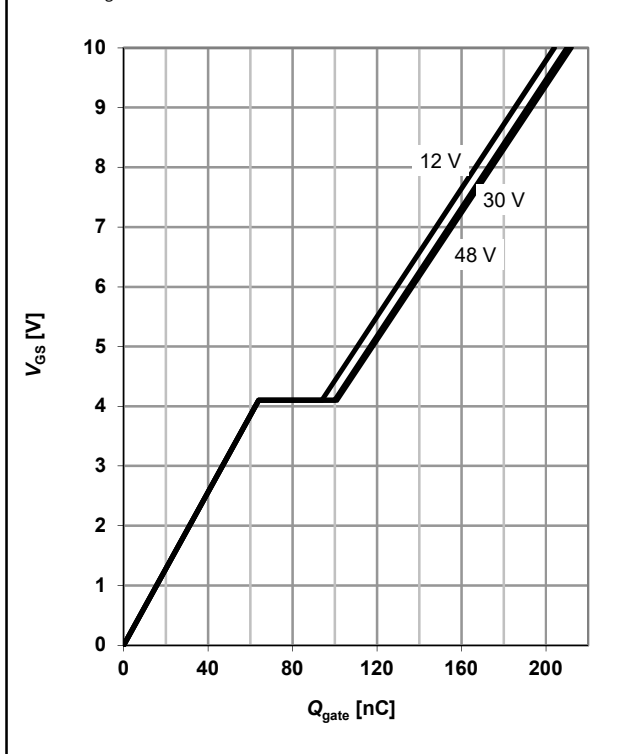
14 Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$; $I_D = 1\text{ mA}$

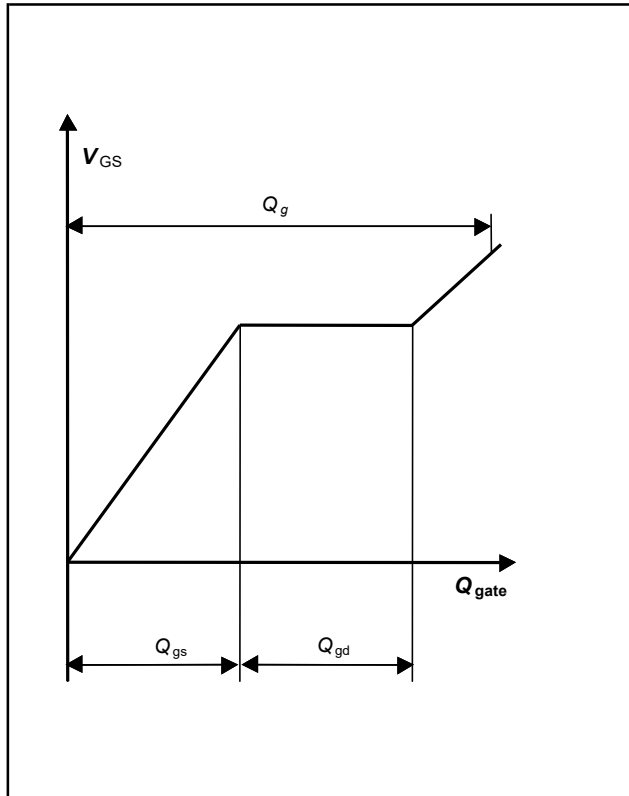


15 Typ. gate charge

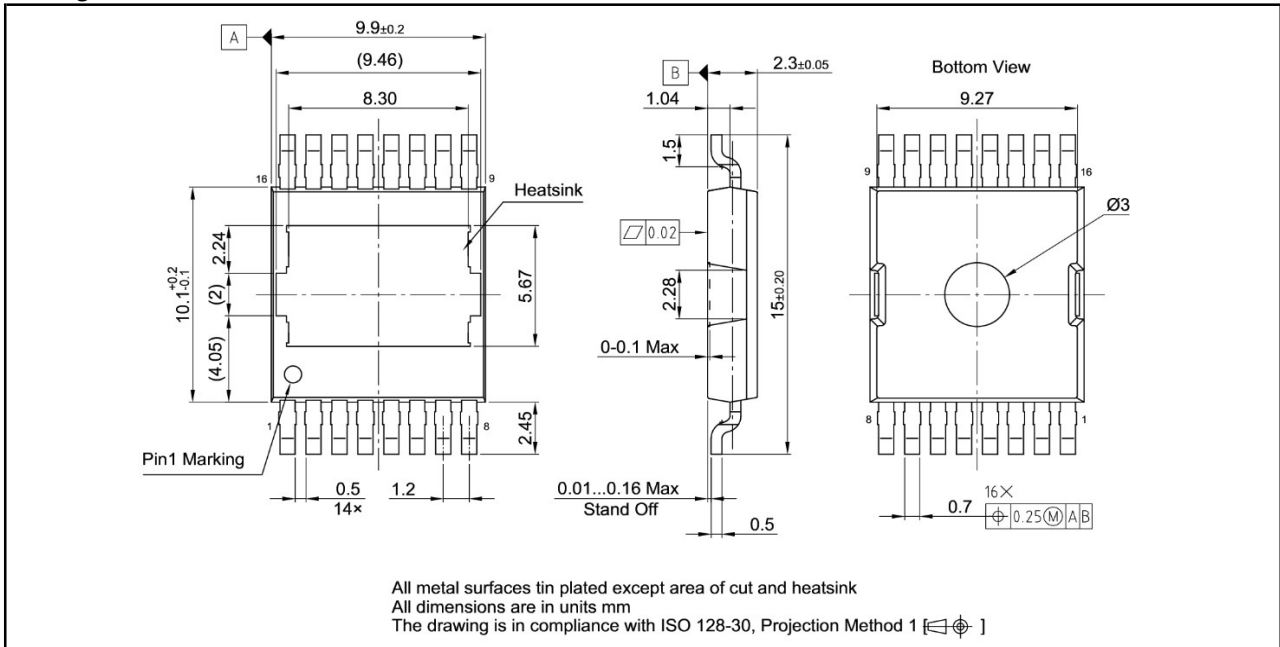
$V_{GS} = f(Q_{gate})$; $I_D = 100\text{ A}$ pulsed; parameter: V_{DD}



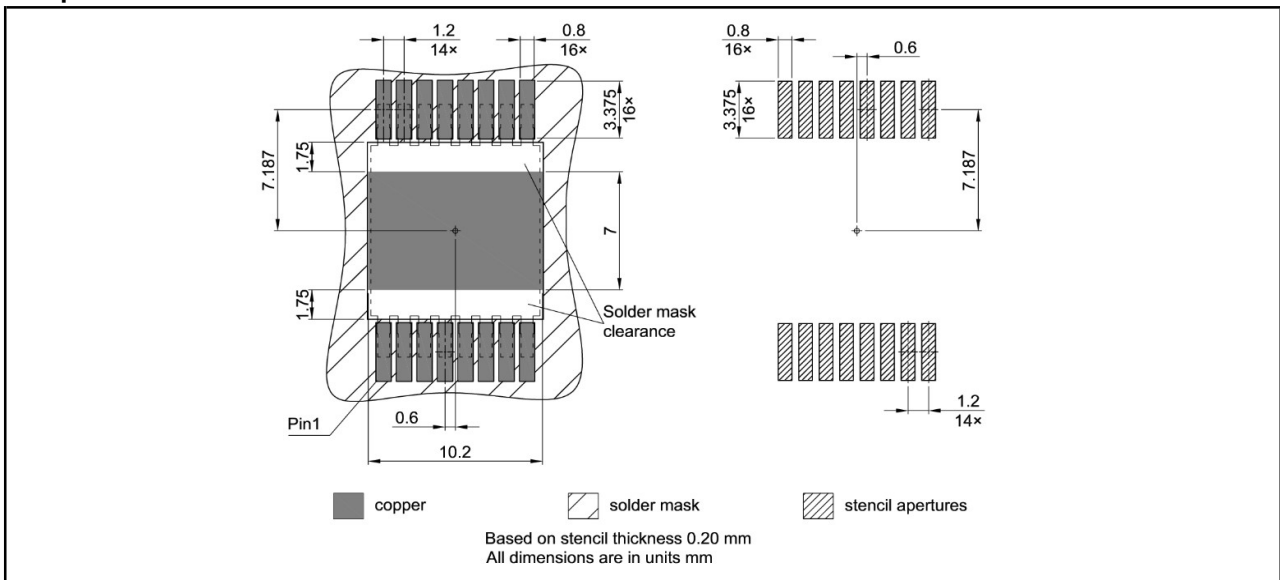
16 Gate charge waveforms



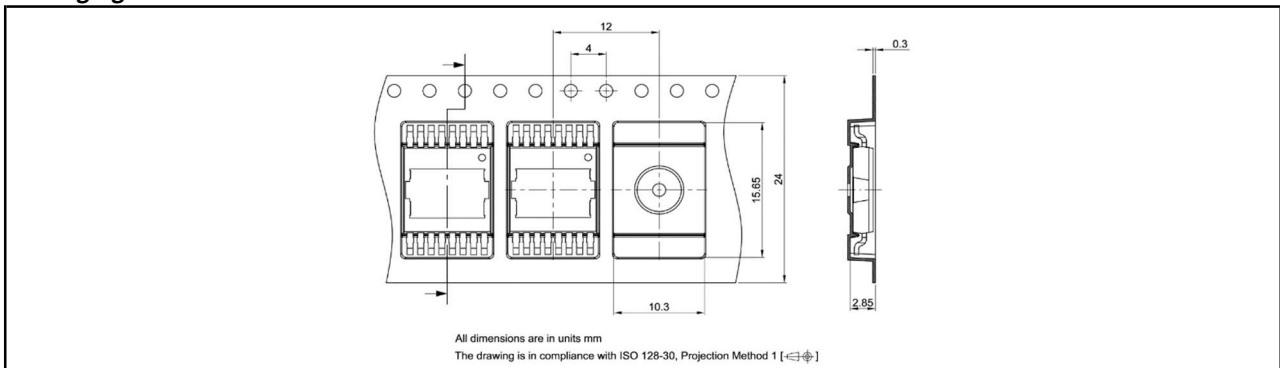
Package Outline



Footprint



Packaging



Revision History

Revision	Date	Changes
Revision 1.0	2023-02-07	Final data sheet
Revision 1.01	2023-09-06	Reduced typical on-state resistance $R_{DS(on)}$

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